

Chipset Delivers Impressive Efficiency for High Frequency DC-DC Switching Applications



International Rectifier, IR introduces the IRF6706S2PbF and IRF6798MPbF DirectFET® MOSFET chipset that provides best-in-class efficiency for 12V input synchronous buck applications including servers, desktops, and notebooks. Featuring the company's latest generation MOSFET silicon technology, the IRF6706S2PbF and IRF6798MPbF 25V chipset combines industry leading Figures of Merit (FOM) with the superior switching and thermal characteristics of the DirectFET package to provide a solution optimized for high frequency DC-DC switching applications. The IRF6798MPbF Medium Can DirectFET provides on-state resistance (RDS(on)) of less than 1 mOhm enabling extremely high efficiency across the entire load range. The new device features a monolithically integrated Schottky diode that reduces losses associated with body diode conduction and reverse recovery losses to further enhance the overall performance of the solution. The IRF6798MPbF also delivers ultra low gate resistance (Rg) of 0.25Ohm to eliminate Cdv/dt related shoot through. The IRF6706S2PbF Small Can DirectFET also features low charge and low RDS(on) to reduce switching and conduction losses, and extremely low Rg for fast switching.

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